

IN THE CLAIMS:

Please amend the claims as listed on the attached Listing of Claims.

LISTING OF CLAIMS

Claims 1-33 (Canceled)

34. (Amended) A method of making a GaN single crystal substrate ~~according to claim 1~~,
comprising:

a mask layer forming step of forming on a GaAs substrate a mask layer having a plurality
of opening windows disposed separate from each other;

a buffer layer forming step of forming a buffer layer on said GaAs substrate in said
opening windows of said mask layer; and

an epitaxial layer growing step of growing on said mask layer an epitaxial layer made of
GaN,

wherein said epitaxial layer is grown in said epitaxial layer growing step so as to form an
ingot of GaN single crystal,

said method further comprising a cutting step of cutting said ingot into a plurality of
sheets.

35. (Amended) A method of making a GaN single crystal substrate ~~according to claim 1~~,
comprising:

a mask layer forming step of forming on a GaAs substrate a mask layer having a plurality
of opening windows disposed separate from each other;

a buffer layer forming step of forming a buffer layer on said GaAs substrate in said
opening windows of said mask layer; and

an epitaxial layer growing step of growing on said mask layer an epitaxial layer made of
GaN,

wherein said epitaxial layer is grown in said epitaxial layer growing step so as to form an
ingot of GaN single crystal,

said method further comprising a cleaving step of cleaving said ingot into a plurality of
sheets.

36. (Amended) A method of making a GaN single crystal substrate comprising:

an ingot forming step of growing on the a GaN single crystal substrate obtained by the ~~method according to claim 1~~ executing a (i) a mask layer forming step of forming on a GaAs substrate a mask layer having a plurality of opening windows disposed separate from each other, (ii) a buffer layer forming step of forming a buffer layer on said GaAs substrate in said opening windows of said mask layer, and (iii) an epitaxial layer growing step of growing on said mask layer an epitaxial layer made of GaN to provide an epitaxial layer made of GaN so as to form an ingot of GaN single crystal; and

a cutting step of cutting said ingot into a plurality of sheets.

37. (Amended) A method of making a GaN single crystal substrate comprising:

an ingot forming step of growing on the a GaN single crystal substrate obtained by the ~~method according to claim 1~~ executing a (i) a mask layer forming step of forming on a GaAs substrate a mask layer having a plurality of opening windows disposed separate from each other, (ii) a buffer layer forming step of forming a buffer layer on said GaAs substrate in said opening windows of said mask layer, and (iii) an epitaxial layer growing step of growing on said mask layer an epitaxial layer made of GaN to provide an epitaxial layer made of GaN so as to form an ingot of GaN single crystal; and

a cleaving step of cleaving said ingot into a plurality of sheets.

Claim 38. (Original) A method of making a GaN single crystal substrate comprising:

an ingot forming step of forming an ingot of GaN single crystal by growing an epitaxial layer made of GaN on a GaN single crystal employed as a seed crystal; and

a cutting step of cutting said ingot into a plurality of sheets.

Claim 39. (Original) A method of making a GaN single crystal substrate comprising:

an ingot forming step of forming an ingot of GaN single crystal by growing an epitaxial layer made of GaN on a GaN single crystal employed as a seed crystal; and

a cleaving step of cleaving said ingot into a plurality of sheets.

Claims 40-58 (Cancelled)